

High-reliability discrete products and engineering services since 1977

## 1N4448

#### SILICON SWITCHING DIODE

#### **FEATURES**

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

#### **MAXIMUM RATINGS**

Parameter	Symbol	Conditions	Min	Max	Unit
Repetitive peak reverse voltage	$V_{RRM}$		-	100	V
Continous reverse voltage	$V_R$		-	100	V
Continuous forward current <sup>(1)</sup>	I <sub>F</sub>		-	200	mA
Repeptive peak forward current	I <sub>FRM</sub>			450	mA
Non-repetitive peak forward current	I <sub>FSM</sub>	Square wave; T <sub>J</sub> = 25°C prior to surge			
		t = 1μs	-	4	
		t = 1ms	-	1	Α
		t = 1s	-	0.5	
Storage temperature	T <sub>stg</sub>		-65	+200	°C
Junction temperature	Tı		-	200	°C

Note 1: Device mounted on a FR4 printed-circuit board; lead length 10mm

ELECTRICAL CHARACTERISTICS (@TJ = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min	Max	Unit
Forward voltage					
	$V_{F}$	I <sub>F</sub> = 5mA	0.62	0.72	V
		I <sub>F</sub> = 100mA	-	1	
Reverse current	I <sub>R</sub>	V <sub>R</sub> = 20V	-	25	nA
Reverse current	I <sub>R</sub>	V <sub>R</sub> = 20V, T <sub>J</sub> = 100°C	-	3	μΑ
Reverse current	I <sub>R</sub>	V <sub>R</sub> = 20V, 25°C I <sub>R</sub> , T <sub>J</sub> = 150°C	-	50	μΑ
Diode capacitance	C <sub>d</sub>	$f = 1MHz, V_R = 0V$	-	4	pF
Reverse recovery time	t <sub>rr</sub>	When switched from $I_F = 10$ mA to $I_R =$		4	
		$60$ mA, $R_L$ = $100$ Ω measured at $I_R$ = $1$ mA	-	4	ns
Forward recovery voltage	V <sub>fr</sub>	When switched from $I_F$ = 50mA, $t_r$ = 20ns -		2.5	V

#### THERMAL CHARACTERISTCS

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Parameter	Symbol	Conditions	Value	Unit		
Thermal resistance junction to tie-point	R <sub>th(j-tp)</sub>	Lead length 10mm	240	K/W		
Thermal resistance from junction to ambient	R <sub>th(j-a)</sub>	Lead length 10mm <sup>(1)</sup>	350	K/W		

Note 1: Device mounted on a printed-circuit board without metallization pad.



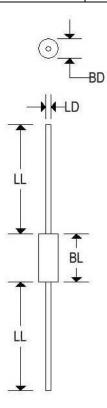
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#### MECHANICAL CHARACTERISTICS

Case:	DO-35	
Marking:	Alpha-numeric	
Polarity:	Cathode band	



	DO-35					
	Inches		Millimeters			
	Min	Max	Min	Max		
BD	0.055	0.090	1.400	2.290		
BL	0,120	0.200	3.050	5.080		
LD	0.018	0.022	0.460	0.560		
LL	1.000	1.500	25.400	38,100		